

BYV410-600 Dual enhanced ultrafast power diode Rev. 2 — 5 August 2011

Product data sheet

Product profile 1.

1.1 General description

Dual enhanced ultrafast power diode in a SOT78 (TO-220AB) plastic package.

1.2 Features and benefits

- High thermal cycling performance
- Low on state losses

- Low thermal resistance
- Soft recovery characteristic minimizes power consuming oscillations

1.3 Applications

■ Dual mode (DCM and CCM) PFC

■ Power Factor Correction (PFC) for Interleaved Topology

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{O(AV)}	average output current	square-wave pulse; δ = 0.5; $T_{mb} \le 92$ °C; both diodes conducting; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	20	Α
Static cha	aracteristics					
V _F	forward voltage	I _F = 10 A; T _j = 150 °C	-	1.3	1.9	V
		$I_F = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 4	-	1.4	2.1	V
Dynamic	characteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 5	-	20	35	ns
Q _r	recovered charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V};$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	15	28	nC



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode	mb	A1 A2
3	A2	anode 2		K
mb	К	mounting base; cathode	1 2 3	sym125
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV410-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
$I_{O(AV)}$	average output current	square-wave pulse; δ = 0.5; $T_{mb} \le 92$ °C; both diodes conducting; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	20	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; T_{mb} ≤ 108 °C; per diode	-	20	Α
I _{FSM}	non-repetitive peak forward current	t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	-	132	Α
		t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	-	120	Α
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C

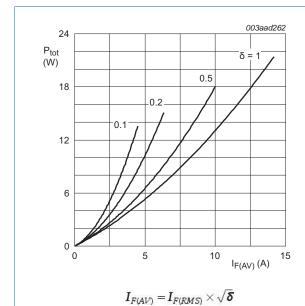
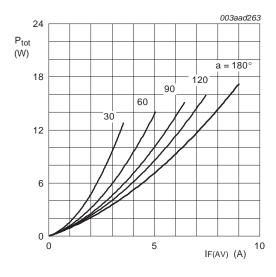


Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a =form factor $= I_{T(RMS)} / I_{T(AV)}$

Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; per diode; see Figure 3	-	-	2.4	K/W
		with heatsink compound; both diodes conducting	-	-	1.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	60	-	K/W

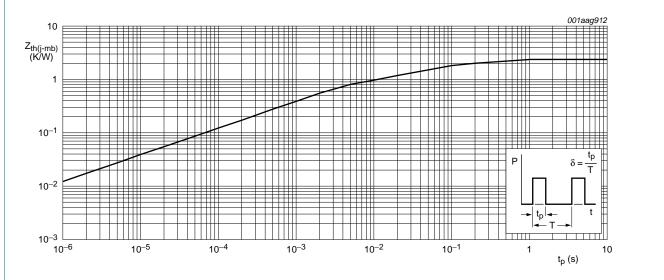


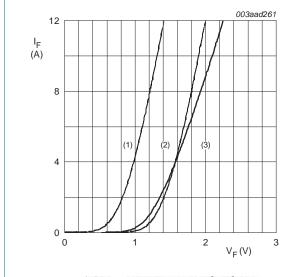
Fig 3. Transient thermal impedance from junction to mounting base per diode as a function of pulse width

Dual enhanced ultrafast power diode

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V_{F}	forward voltage	I _F = 10 A; T _j = 150 °C	-	1.3	1.9	V
		$I_F = 10 \text{ A}$; $T_j = 25 \text{ °C}$; see Figure 4	-	1.4	2.1	V
I _R reverse current		V _R = 600 V	-	13	50	μΑ
		V _R = 600 V; T _j = 100 °C	-	1	1.5	mA
Dynamic ch	naracteristics					
Q _r	recovered charge	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	15	28	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 5	-	20	35	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; see Figure 5	-	1.4	1.9	Α
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; see Figure 6	-	3.2	-	V



(1) $T_j = 150 \, ^{\circ}C$; typical values (2) $T_j = 150 \, ^{\circ}C$; maximum values

(3) $T_j = 25$ °C; maximum values

Fig 4. Forward current as a function of forward voltage

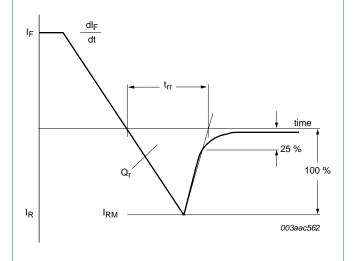
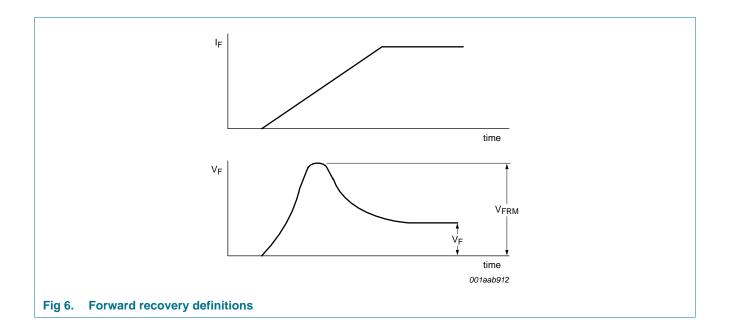


Fig 5. Reverse recovery definitions; ramp recovery

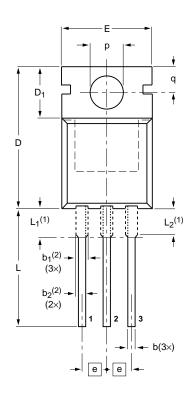
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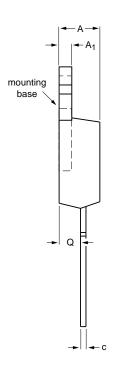


BYV410-600

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

UNI	ГА	A ₁	b	b ₁ (2)	b ₂ (2)	С	D	D ₁	E	е	L	L ₁ (1)	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES		ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig 7. Package outline SOT78 (TO-220AB)

BYV410-600

BYV410-600 **NXP Semiconductors**

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Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BYV410-600 v.2	20110805	Product data sheet	-	BYV410-600_1			
Modifications:	Modifications: • Various changes to content.						
BYV410-600_1	20090629	Product data sheet	-	-			

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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